
2SD1421

Silicon NPN Epitaxial

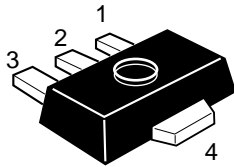
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Application

Low frequency power amplifier

Outline

UPAK



1. Base
2. Collector
3. Emitter
4. Collector (Flange)

2SD1421

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	V _{CBO}	180	V
Collector to emitter voltage	V _{CEO}	160	V
Emitter to base voltage	V _{EBO}	5	V
Collector current	I _C	1.5	A
Collector peak current	i _{C(peak)} *1	3	A
Collector power dissipation	P _C *2	1	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 ms, Duty cycle ≤ 20%

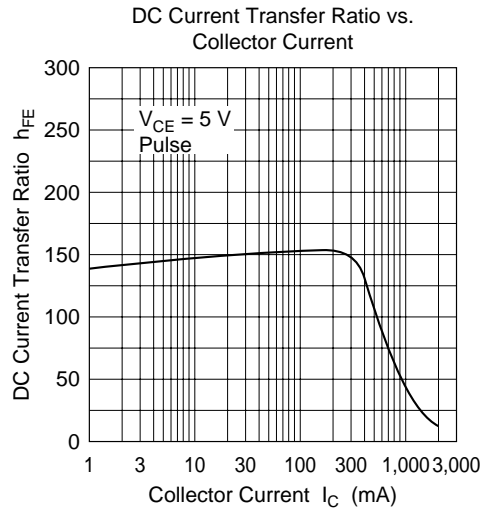
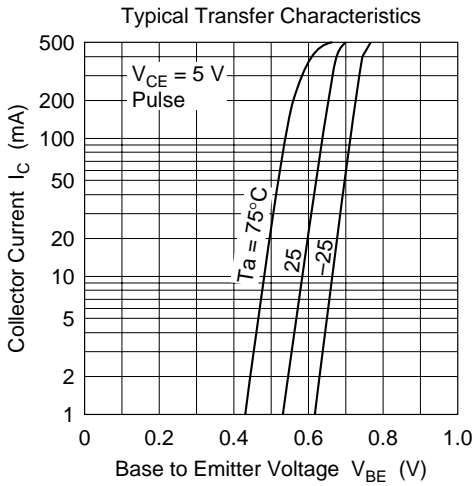
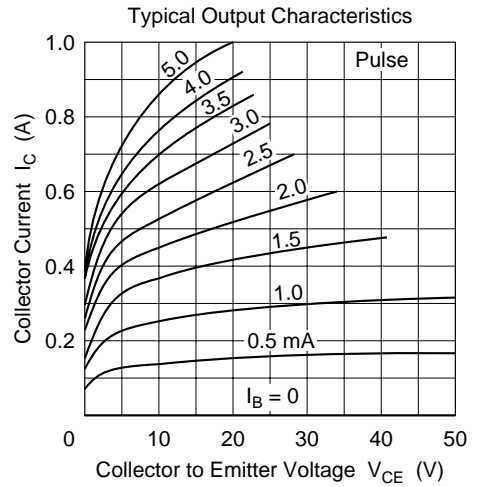
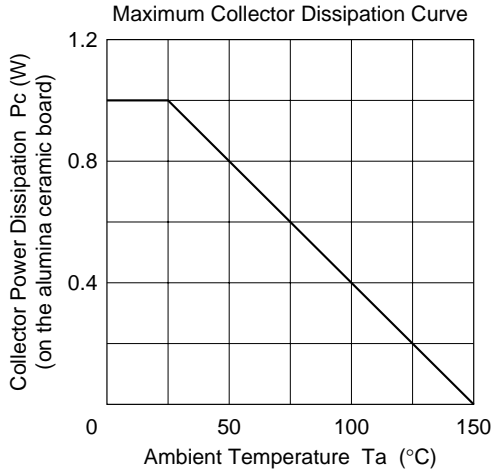
2. Value on the alumina ceramic board (12.5 x 20 x 0.7 mm)

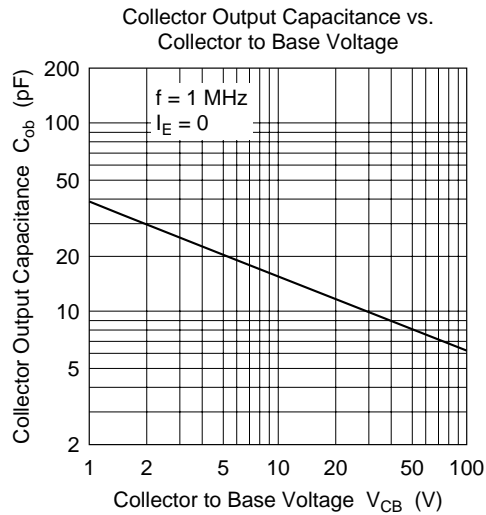
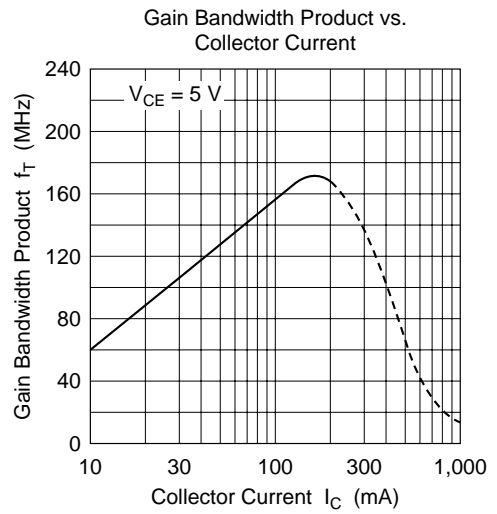
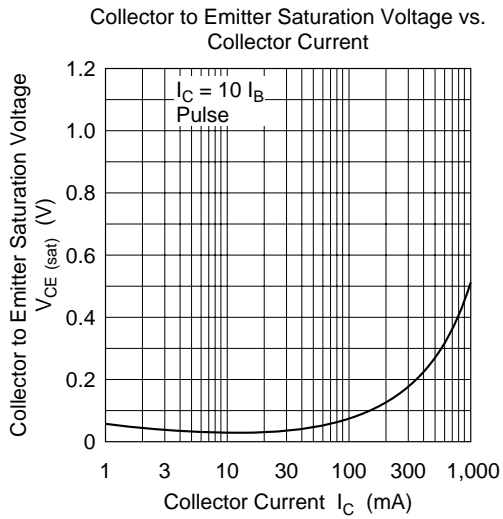
Electrical Characteristics (Ta = 25°C)

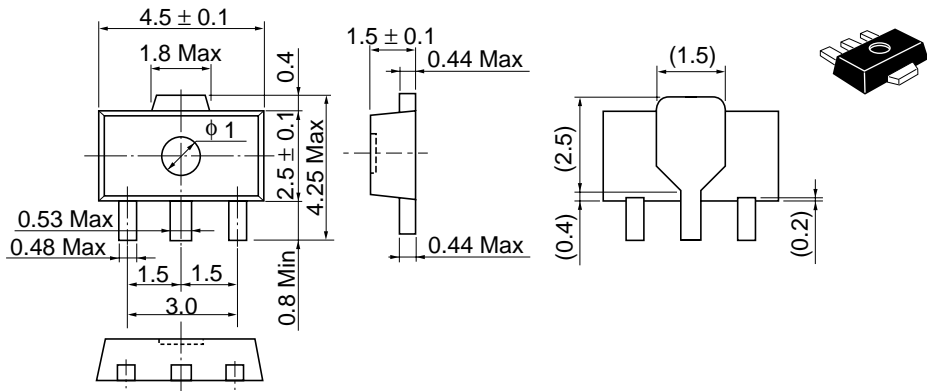
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	V _{(BR)CBO}	180	—	—	V	I _C = 1 mA, I _E = 0
Collector to emitter breakdown voltage	V _{(BR)CEO}	160	—	—	V	I _C = 10 mA, R _{BE} = ∞
Emitter to base breakdown voltage	V _{(BR)EBO}	5	—	—	V	I _E = 1 mA, I _C = 0
Collector cutoff current	I _{CBO}	—	—	10	μA	V _{CB} = 160 V, I _E = 0
DC current transfer ratio	h _{FE1} *1	60	—	200		V _{CE} = 5 V, I _C = 0.15 A
	h _{FE2}	30	—	—		V _{CE} = 5 V, I _C = 0.5 A
Collector to emitter saturation voltage	V _{CE(sat)}	—	—	1.0	V	I _C = 0.5 A, I _B = 50 mA, Pulse voltage
Base to emitter voltage	V _{BE}	—	—	0.9	V	V _{CE} = 5 V, I _C = 0.15 A, Pulse

Note: 1. The 2SD1421 is grouped by h_{FE1} as follows.

Mark	ED	EE
h _{FE1}	60 to 120	100 to 200







Hitachi Code	UPAK
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.050 g

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